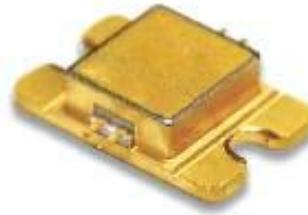


Performance

- Technology: 0.25um Power GaN HEMT
- Frequency: 0.35~2.0GHz
- Typical Pout : $\geq 37\text{dBm(CW)}$
- Typical Gain: $\geq 30\text{dB}$
- Typical PAE: $\geq 31\%$
- Bias: 28V/-2~-2.5V@0.5A
- Package: Metal Ceramic

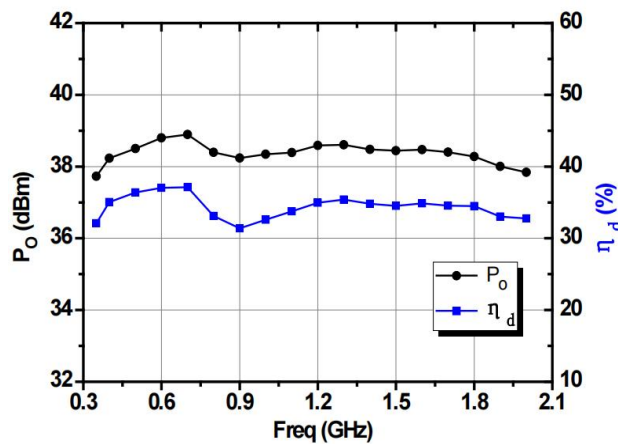


Electrical Specifications ($T_A=25^\circ\text{C}$, $V_d=28\text{V}$, $I_{dq}=0.5\text{A}$, $F: 0.35\sim 2.0\text{GHz}$, $P_{in}=7\text{dBm}$)

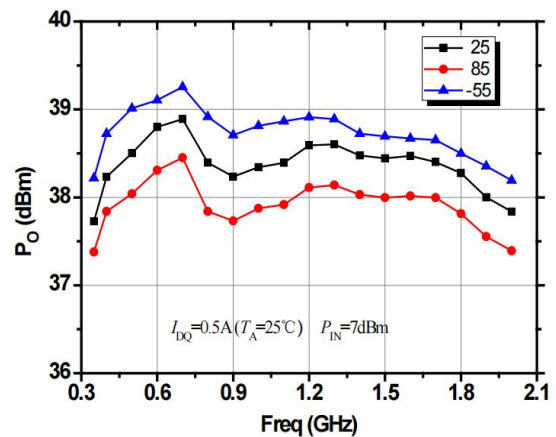
Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	37	-	-	dBm
Gp	Power Gain	30	-	-	dB
η_{add}	Power Added Efficiency	31	-	-	%
ΔGp	Gain Flatness	-	-	± 0.6	dB
Rth	Thermal Resistance	-	3	-	$^\circ\text{C/W}$

Test Curves

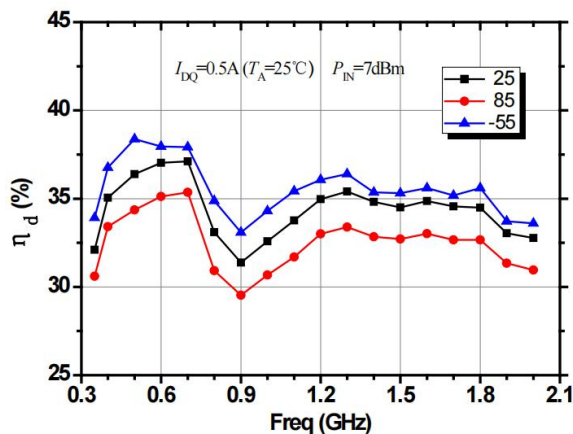
Pout, η_{add} &Freq.



Pout&Freq. @ Different Temp.



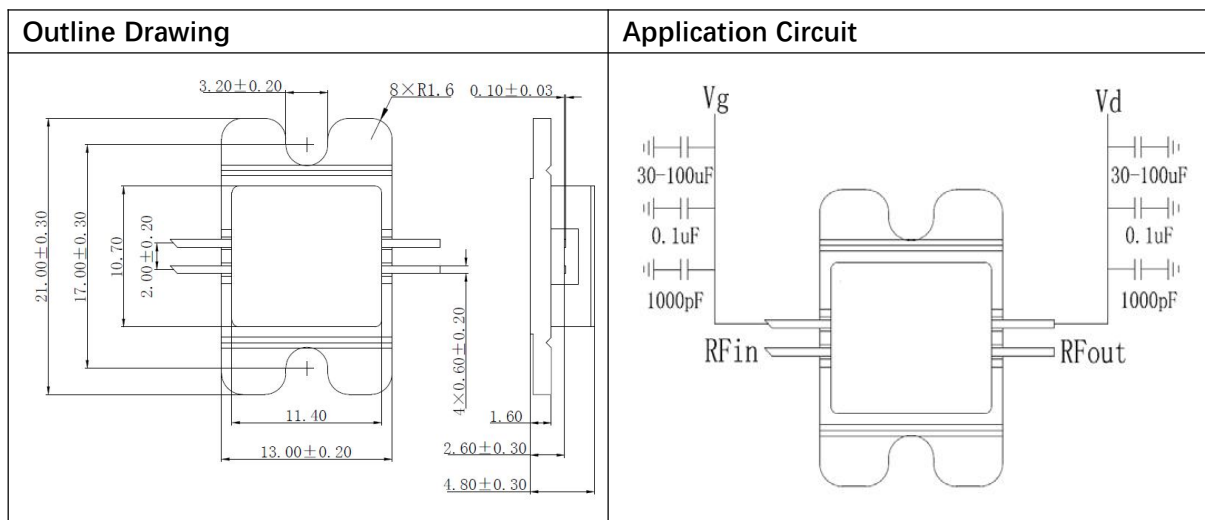
η_{add} &Freq. @ Different Temp.



Absolute Max Ratings (T_A=25°C)

Symbol	Parameter	Value	Remark
V _d	Drain Voltage	40V	
V _g	Grid Voltage	-5V	
P _d	DC Dissipation	300W	25°C
T _{ch}	Channel Temperature	225°C	【1】
T _m	Mounting Temperature	300°C	1 min, N ₂ Protection
T _{stg}	Storage Temperature	-55~175°C	

【1】 Exceeding any one or combination of these limits may cause permanent damage.



Note:

- (1) The input and output impedance values of this product are both 50 ohms;
- (2) Connect the circuit according to the diagram, pay attention to anti-static, and ensure good grounding and heat dissipation when using power devices;
- (3) Please strictly follow the order of adding negative electricity first and then positive electricity in the power-on sequence. When de-energizing, first reduce the drain voltage and then reduce the gate voltage;
- (4) This product is an electrostatic sensitive device. It is necessary to pay attention to electrostatic protection during storage and use, and it needs to be well grounded when using it.